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November 2013

### **FQP12P10**

## P-Channel QFET® MOSFET

-100 V, -11.5 A, 290 mΩ

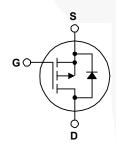
### **Description**

These P-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology. This advanced technology has been especially tailored to minimize onstate resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as audio amplifier, high efficiency switching DC/DC converters, and DC motor control.

#### **Features**

- -11.5 A, -100 V,  $R_{DS(on)}$  = 290 m $\Omega$  (Max.) @  $V_{GS}$  = -10 V,  $I_D = -5.75 A$
- Low Gate Charge (Typ. 21 nC)
- · Low Crss (Typ. 65 pF)
- 100% Avalanche Tested
- 175°C Maximum Junction Temperature Rating





#### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP12P10	Unit
V <sub>DSS</sub>	Drain-Source Voltage		-100	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	C)	-11.5	Α
	- Continuous (T <sub>C</sub> = 100°C)		-8.1	Α
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	-46	Α
V <sub>GSS</sub>	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	370	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	-11.5	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	7.5	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	-6.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C)		75	W
	- Derate above 25°C		0.5	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +175	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

#### **Thermal Characteristics**

Symbol	Parameter	FQP12P10	Unit	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	2.0	°C/W	
$R_{\theta CS}$	Thermal Resistance, Case-to-Sink, Typ.	0.5	°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W	

### **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP12P10	FQP12P10	TO-220	Tube	N/A	N/A	50 units

### **Electrical Characteristics** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Unit
Off Cha	racteristics					
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$	-100			V
$\Delta BV_{DSS}$ / $\Delta T_{J}$	Breakdown Voltage Temperature Coefficient	$I_D$ = -250 $\mu$ A, Referenced to 25°C		-0.1		V/°C
I <sub>DSS</sub>	Zara Cata Valtana Duais Comunant	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}$			-1	μА
Zero	Zero Gate Voltage Drain Current	$V_{DS} = -80 \text{ V}, T_{C} = 150^{\circ}\text{C}$			-10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	$V_{GS} = -30 \text{ V}, V_{DS} = 0 \text{ V}$			-100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nA
On Cha	racteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	-2.0		-4.0	٧
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = -10 V, I <sub>D</sub> = -5.75 A		0.24	0.29	Ω
9 <sub>FS</sub>	Forward Transconductance	$V_{DS} = -40 \text{ V}, I_{D} = -5.75 \text{ A}$		6.7		S
Dynami	c Characteristics					
C <sub>iss</sub>	Input Capacitance	$V_{DS} = -25 \text{ V}, V_{GS} = 0 \text{ V},$		620	800	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0 MHz		220	290	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			65	85	pF
Switchi	ng Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = -50 V, I <sub>D</sub> = -11.5 A,		15	40	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		160	330	ns
t <sub>d(off)</sub>	Turn-Off Delay Time	_		35	80	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		60	130	ns
$Q_g$	Total Gate Charge	$V_{DS} = -80 \text{ V}, I_{D} = -11.5 \text{ A},$		21	27	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = -10 V	/	4.6		nC
Q <sub>gd</sub>	Gate-Drain Charge	(Note 4)		11.5		nC
Drain-S	ource Diode Characteristics a	nd Maximum Ratings				
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				-11.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				-46	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -11.5 A			-4.0	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = -11.5 A,		110		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> / dt = 100 A/μs		0.47		μС

- Repetitive rating: pulse-width limited by maximum junction temperature. 2. L = 4.2 mH,  $I_{AS}$  = -11.5 A,  $V_{DD}$  = -25 V,  $R_G$  = 25  $\Omega$ , starting  $T_J$  = 25°C. 3.  $I_{SD}$  < -11.5 A, di/dt < 300 A/ $\mu$ s,  $V_{DD}$  < BV $_{DSS}$ , starting  $T_J$  = 25°C. 4. Essentially independent of operating temperature.

### **Typical Characteristics**

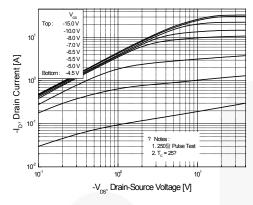


Figure 1. On-Region Characteristics

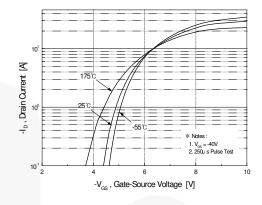


Figure 2. Transfer Characteristics

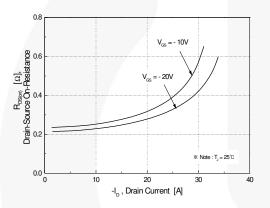


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

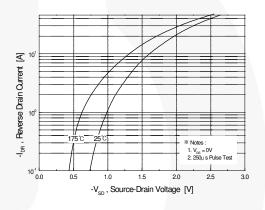


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

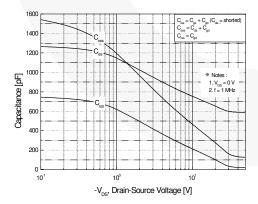


Figure 5. Capacitance Characteristics

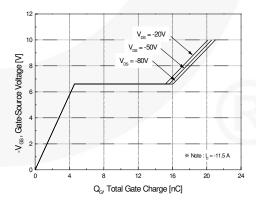


Figure 6. Gate Charge Characteristics

### Typical Characteristics (Continued)

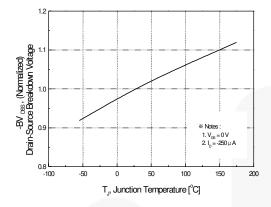


Figure 7. Breakdown Voltage Variation vs. Temperature

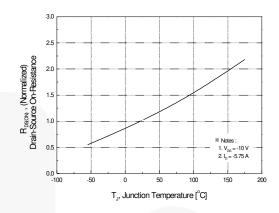


Figure 8. On-Resistance Variation vs. Temperature

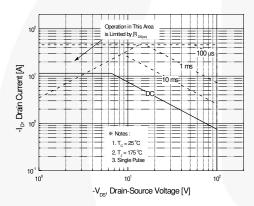


Figure 9. Maximum Safe Operating Area

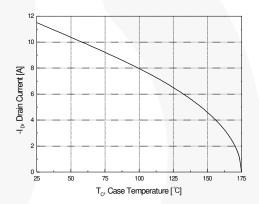


Figure 10. Maximum Drain Current vs. Case Temperature

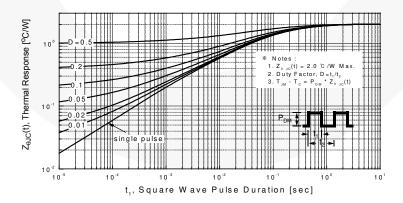


Figure 11. Transient Thermal Response Curve

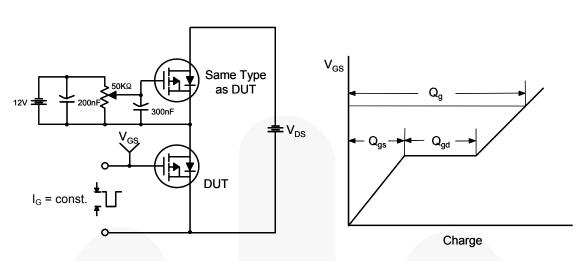


Figure 12. Gate Charge Test Circuit & Waveform

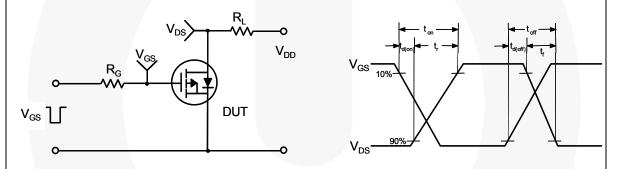


Figure 13. Resistive Switching Test Circuit & Waveforms

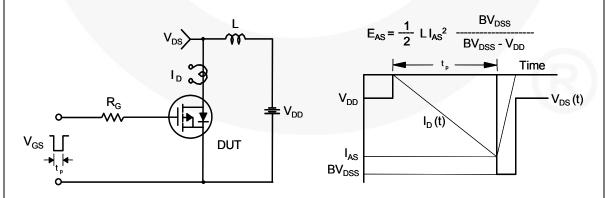
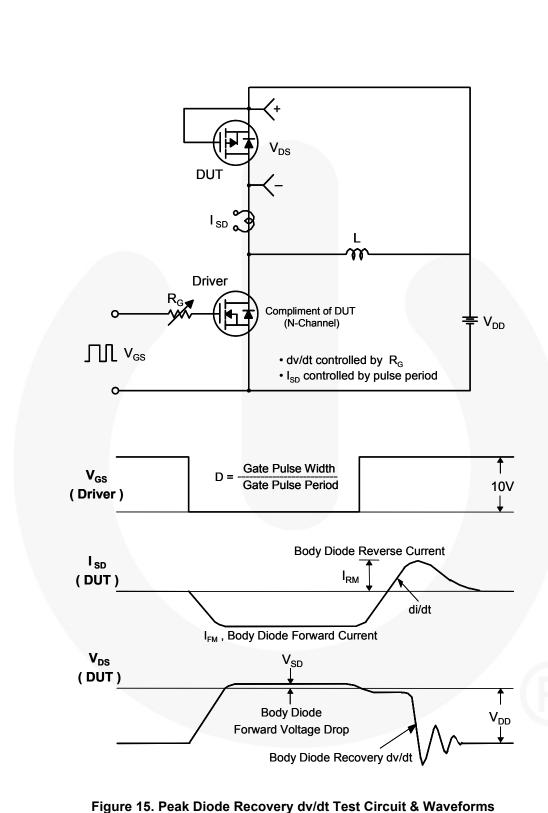


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



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#### **Mechanical Dimensions**

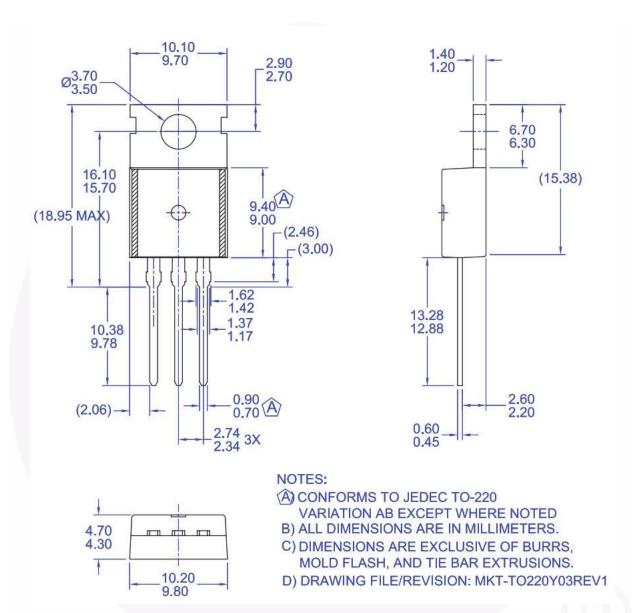


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

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